

NPN 1.0A 50V Middle Power Transistor

Parameter	Value
$V_{\sf CEO}$	50V
I _C	1.0A

Features

1) Suitable for Middle Power Driver

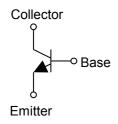
2) Complementary PNP Types: 2SAR513P

3) Low V_{CE(sat)}

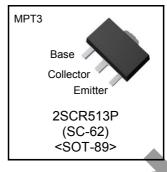
 $V_{CE(sat)}$ =0.35V(Max.) (I_C/I_B =500mA/25mA)

4) Lead Free/RoHS Compliant.

•Inner circuit



Outline



Applications

Motor driver , LED driver Power supply

Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
2SCR513P	MPT3	4540	T100	180	12	1,000	NC

● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Values	Unit
Collector-base voltage		V _{CBO}	50	V
Collector-emitter voltage		V _{CEO}	50	V
Emitter-base voltage		V _{EBO}	6	V
Collector current	DC	I _C	1.0	Α
Collector current	Pulsed	I _{CP} *1	2.0	Α
Power dissipation		P _D *2	0.5	W
		P _D *3	2.0	W
Junction temperature		T _j	150	°C
Range of storage temperature		T _{stg}	−55 to +150	°C

^{*1} Pw=10ms, single pulse

^{*2} Each terminal mounted on a reference land

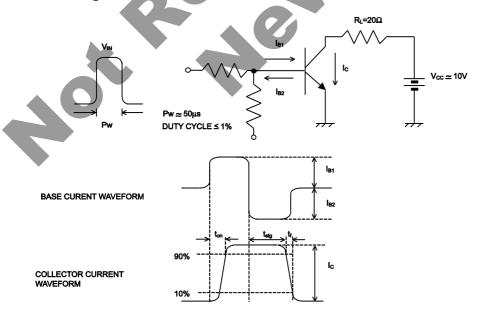
^{*3} Mounted on a ceramic board (40×40×0.7mm)

●Electrical characteristics(Ta = 25°C)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 1mA	50	-	-	V
Collector-base breakdown voltage	BV _{CBO}	I _C = 100μA	50	-	-	V
Emitter-base breakdown voltage	BV _{EBO}	I _E = 100μA	6	ı	-	V
Collector cut-off current	I _{CBO}	V _{CB} = 50V	ı	-	(-)	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 4V	-	-	1	μА
Collector-emitter saturation voltage	V _{CE(sat)} *1	I _C = 500mA, I _B = 25mA		0.13	0.35	V
DC current gain	h _{FE}	$V_{CE} = 2V$, $I_C = 50$ mA	180	-	450	-
Transition frequency	f _T	$V_{CE} = 10V$, $I_{E} = -200$ mA f=100MH _Z	-	360	-	MHz
Output capacitance	C _{ob}	$V_{CB} = 10V, I_{E} = 0A,$ f = 1MHz	-	7	-	pF
Turn-on time	t _{on} *2	I _C =0.5A	Ŷ	40	-	ns
Storage time	t _{stg} *2	I _{B1} =50mA I _{B2} = -50mA	-	410	-	ns
Fall time	t _f *2	V _{CC} ≃10V	-	75	-	ns

^{*1} Pulsed

•Switching time test circuit



^{*2} See switching time test circuit

●Electrical characteristic curves(Ta = 25°C)

Fig.1 Ground Emitter Propagation Characteristics

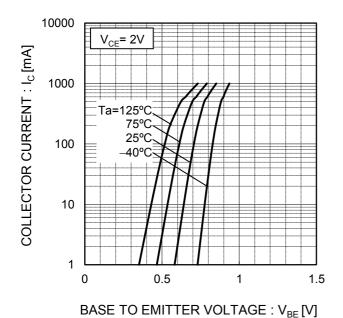
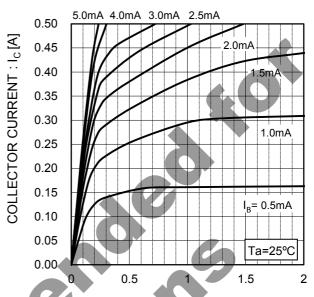


Fig.2 Typical Output Characteristics



COLECTOR TO EMITTE VOLTAGE : $V_{CE}[V]$

Fig.3 DC Current Gain vs. Collector Current(I)

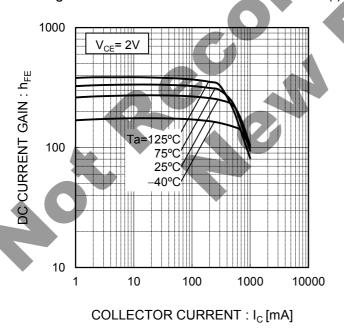
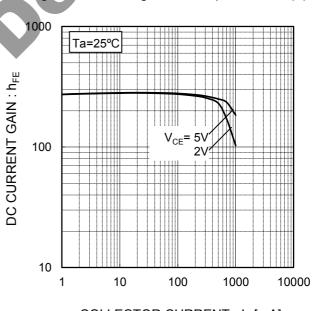
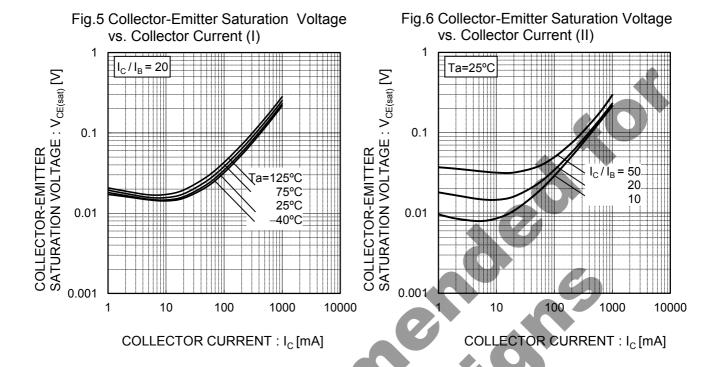


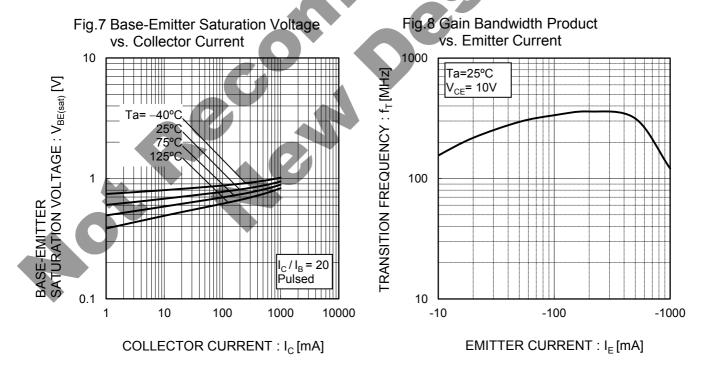
Fig.4 DC current gain vs. output current (II)



COLLECTOR CURRENT : I_C [mA]

●Electrical characteristic curves(Ta = 25°C)

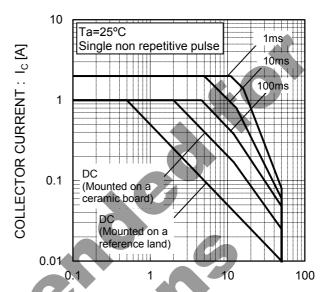




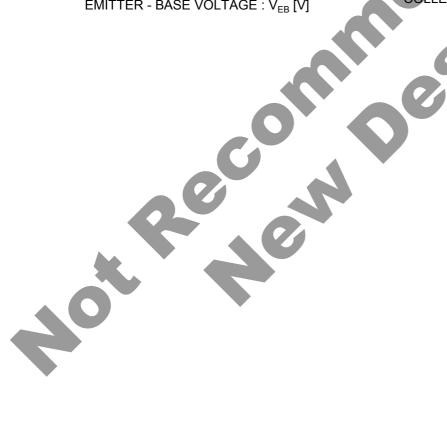
●Electrical characteristic curves(Ta = 25°C)

Fig.9 Emitter input capacitance vs. **Emitter-Base Voltage** Collector output capacitance vs. COLLECTOR OUTPUT CAPACITANCE: Cob [pF] EMITTER INPUT CAPACITANCE: Cib [pF] Collector-Base Voltage 1000 Ta=25°C f=1MHz I_E=0A $I_{C}^{-}=0A$ 100 10 0.1 10 COLLECTOR - BASE VOLTAGE : V_{CB} [V] EMITTER - BASE VOLTAGE : VEB [V]

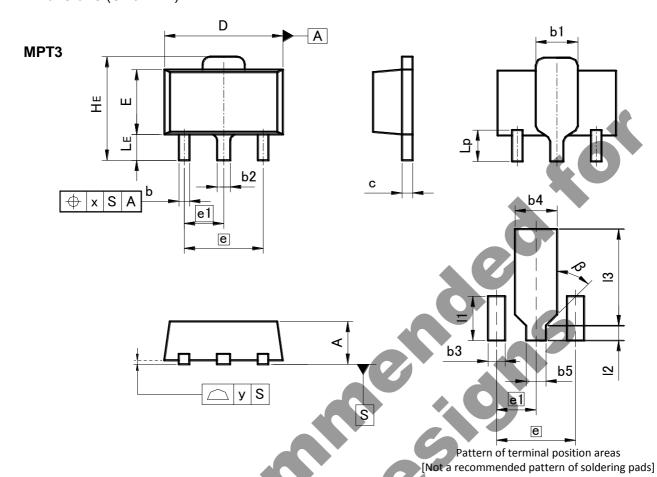
Fig.10 Safe Operating Area



COLLECTOR TO EMITTER VOLTAGE : $V_{CE}[V]$



●Dimensions (Unit: mm)



		·				
DIM	MILIM	ETERS	INC	INCHES		
DIIVI	MIN	MAX	MIN	MAX		
Α	1.40	1.50	0.055	0.059		
b	0.30	0.50	0.012	0.020		
b1	1.50	1.70	0.059	0.067		
b2	0.40	0.60	0.016	0.024		
C	0.35	0.50	0.014	0.020		
D	4.40	4.70	0.173	0.185		
E	2.40	2.70	0.094	0.106		
е	3.0	00	0.1	18		
e1	1.	50	0.0	59		
HE	3.70	4.30	0.146	0.169		
LE	0.80	1.20	0.031	0.047		
Lp	1.01	1.41	0.040	0.056		
Х		0.15	-	0.006		
У		0.10	-	0.004		

DIM	MILIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
b3	_	0.65	-	0.026	
b4	-	1.70	_	0.067	
b5	-	0.75	ı	0.030	
l1	-	1.71	1	0.067	
12	-	0.58	1	0.023	
13	_	3.72	-	0.146	
β	45°		45° 45°		

Dimension in mm / inches

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